COMPLIANT

HALOGEN

FREE



www.vishay.com

Vishay Semiconductors

Hyperfast Rectifier, 8 A FRED Pt®



PRIMARY CHARACTERISTICS									
I _{F(AV)}	8 A								
V _R	600 V								
V _F at I _F	1.5 V								
t _{rr} (typ.)	14 ns								
T _J max.	175 °C								
Package	TO-220AC 2L								
Circuit configuration	Single								

FEATURES

- Hyperfast recovery time, extremely low Q_{rr}
- Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- True 2 pin package
- Designed and qualified according to JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage	V _{RRM}		600	V
Average rectified forward current in DC	I _{F(AV)}	T _C = 142 °C	8	۸
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	80	A
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)									
PARAMETER	MIN.	TYP.	MAX.	UNITS					
Breakdown voltage, blocking voltage	V _{BR} , V _R	Ι _R = 100 μΑ	600	-	-	.,			
For and allows	V	I _F = 8 A	=.	2.5	3.4	V			
Forward voltage	V_{F}	I _F = 8 A, T _J = 150 °C	-	1.5	2.0				
Devenue le alcene accoment		$V_R = V_R$ rated	-	0.02	30				
Reverse leakage current	IR	T _J = 150 °C, V _R = V _R rated	-	21	150	μΑ			
Junction capacitance	C _T	V _R = 600 V	-	6	-	pF			
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8	-	nΗ			



www.vishay.com

Vishay Semiconductors

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
Reverse recovery time		$I_F = 1 A, dI_F/dt = 10$	$I_F = 1 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$			18			
		$I_F = 8 \text{ A}, dI_F/dt = 10$	-	15	24				
	t _{rr}	T _J = 25 °C		-	17	-	ns -		
		T _J = 125 °C	$I_F = 8 \text{ A},$ $dI_F/dt = 200 \text{ A/}\mu\text{s},$ $V_R = 390 \text{ V}$	-	33	-			
Dools recovery current		T _J = 25 °C		-	2.6	-	A nC		
Peak recovery current	I _{RRM}	T _J = 125 °C		-	4.3	-			
Devene receiver chare	0	T _J = 25 °C] "	-	22	-			
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	77	-			
Reverse recovery time	t _{rr}		I _F = 8 A,	-	26	-	ns		
Peak recovery current	I _{RRM}	$T_J = 125 ^{\circ}\text{C}$ $dI_F/dt = 600 \text{A/}\mu\text{s},$		-	11	-	Α		
Reverse recovery charge	Q _{rr}		-	150	-	nC			

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	MIN.	TYP.	MAX.	UNITS					
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C			
Thermal resistance, junction-to-case	R _{thJC}		-	2.0	2.6				
Thermal resistance, junction-to-ambient R _{thJA}		Typical socket mount	-	-	70	°C/W			
Typical thermal resistance, case-to-heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-				
Weight			-	2	-	g			
Mounting torque			6 (5)	-	12 (10)	kgf · cm (lbf · in)			
Marking device		Case style TO-220AC 2L	ETX0806						



Vishay Semiconductors

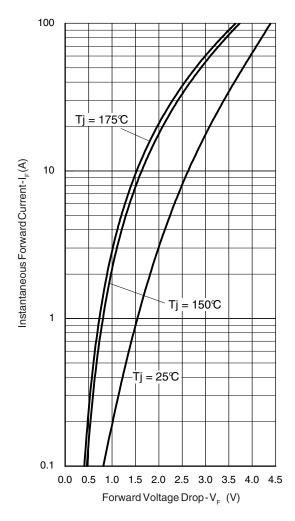


Fig. 1 - Typical Forward Voltage Drop Characteristics

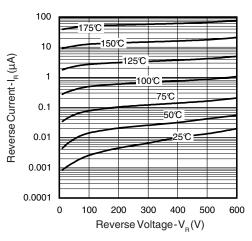


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

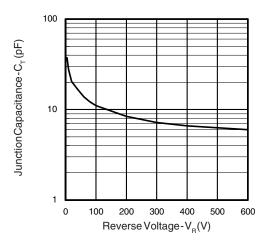


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

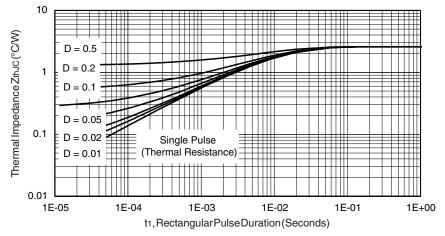


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

www.vishay.com

Vishay Semiconductors

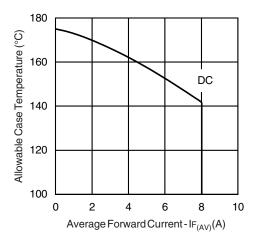


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

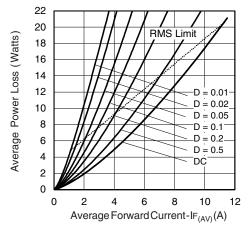


Fig. 6 - Forward Power Loss Characteristics

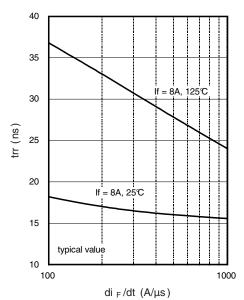


Fig. 7 - Typical Reverse Recovery vs. dl_F/dt

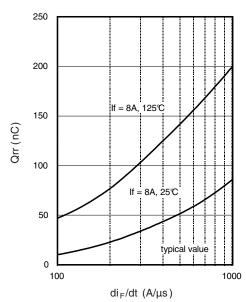
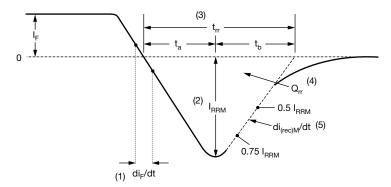


Fig. 8 - Typical Stored Charge vs. dl_F/dt



Vishay Semiconductors

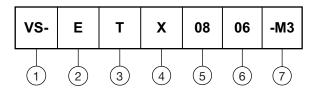


- di_F/dt rate of change of current through zero crossing
- (4) Q_{rr} area under curve defined by t_{rr} and I_{RRM}
- (2) I_{RRM} peak reverse recovery current
- $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (5) di_{(rec)M}/dt peak rate of change of current during t_b portion of t_{rr}

Fig. 9 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



Vishay Semiconductors product

2 - Circuit configuration:

E = single

3 - T = TO-220AC 2L

4 - X = hyperfast recovery time

5 - Current code: 08 = 8 A

6 - Voltage code: 06 = 600 V

7 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

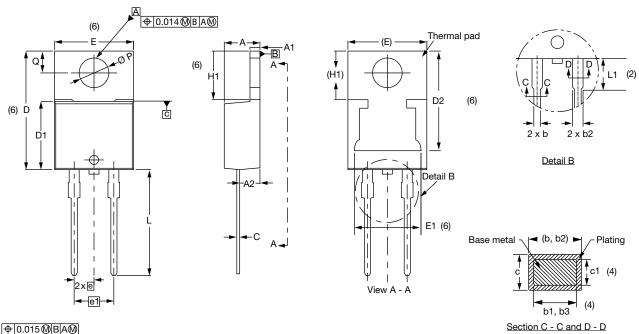
ORDERING INFORMATION (Example)									
PREFERRED P/N BASE QUANTITY PACKAGING DESCRIPTION									
VS-ETX0806-M3	50	Antistatic plastic tubes							

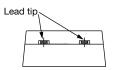
LINKS TO RELATED DOCUMENTS								
Dimensions	www.vishay.com/doc?96156							
Part marking information	www.vishay.com/doc?95391							

Vishay Semiconductors

TO-220AC 2L

DIMENSIONS in millimeters and inches





Conforms to JEDEC® outline TO-220AC

SYMBOL	MILLIMETERS		INCHES		NOTES	NOTES	SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183			D2	11.68	13.30	0.460	0.524	6, 7
A1	1.14	1.40	0.045	0.055			E	10.11	10.51	0.398	0.414	3, 6
A2	2.50	2.92	0.098	0.115			E1	6.86	8.89	0.270	0.350	6
b	0.69	1.01	0.027	0.040			е	2.41	2.67	0.095	0.105	
b1	0.38	0.97	0.015	0.038	4		e1	4.88	5.28	0.192	0.208	
b2	1.20	1.73	0.047	0.068			H1	6.09	6.48	0.240	0.255	6
b3	1.14	1.73	0.045	0.068	4		L	13.52	14.02	0.532	0.552	
С	0.36	0.61	0.014	0.024			L1	3.32	3.82	0.131	0.150	2
c1	0.36	0.56	0.014	0.022	4		ØΡ	3.54	3.91	0.139	0.154	
D	14.85	15.35	0.585	0.604	3		Q	2.60	3.00	0.102	0.118	
D1	8.38	9.02	0.330	0.355				•	•		•	

Notes

- ⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3, and c1 apply to base metal only
- Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2, and E1
- (7) Outline conforms to JEDEC® TO-220, except D2



Legal Disclaimer Notice

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Vishay products are not designed for use in life-saving or life-sustaining applications or any application in which the failure of the Vishay product could result in personal injury or death unless specifically qualified in writing by Vishay. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.